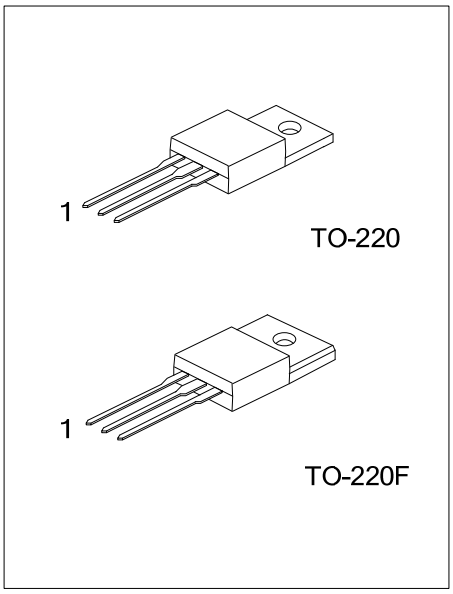
MGBR10L80C

Preliminary ***DIODE***

DUAL MOS GATED BARRIER RECTIFIER



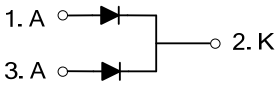
■ DESCRIPTION

The UTC **MGBR10L80C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

* Low forward voltage drop
* High switching speed

■ SYMBOL



■ ORDERING INFORMATION

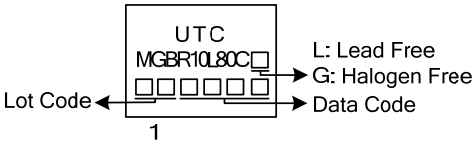
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MGBR10L80CL-TA3-T	MGBR10L80CG-TA3-T	TO-220	A	K	A	Tube
MGBR10L80CL-TF3-T	MGBR10L80CG-TF3-T	TO-220F	A	K	A	Tube

Note: Pin Assignment: A: Anode K: Cathode

MGBR10L80CL-TA3-T

(1)Packing Type	(1) T: Tube
(2)Package Type	(2) TA3: TO-220, TF3: TO-220F
(3)Green Package	(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	80	V
Working Peak Reverse Voltage		V_{RWM}	80	V
Repetitive Peak Reverse Voltage		V_{RRM}	80	V
Average Rectified Output Current Per Device	Per Leg	I_O	5	A
	Total		10	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I_{FSM}	80	A
Operating Junction Temperature		T_J	-65~+150	°C
Storage Temperature		T_{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL RESISTANCES CHARACTERISTICS (PER LEG)

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220	θ_{JC}	2	°C/W
	TO-220F		3.31	

■ ELECTRICAL CHARACTERISTICS (PER LEG) (T_A =25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I_R=0.50mA	80			V
Forward Voltage Drop	V_{FM}	I_F=5A, T_J=25°C			0.72	V
		I_F=5A, T_J=125°C			0.66	V
Leakage Current (Note 1)	I_{RM}	V_R=80V, T_J=25°C			400	μA
		V_R=80V, T_J=125°C			15	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.
2. Thermal resistance junction to case mounted on heatsink.